

## ABSTRACT OF THE DISCLOSURE

09373544, 001, 399

A light-emitting diode includes: a semiconductor substrate; and a layered structure, made of an AlGaInP type compound semiconductor material and provided on the semiconductor substrate. The layered structure includes: a light-emitting structure composed of a pair of cladding layers and an active layer for emitting light provided between the pair of cladding layers; and a current diffusion layer which is lattice-mismatched with the light-emitting structure. A lattice mismatch  $\Delta a/a$  of the current diffusion layer with respect to the light-emitting structure defined by the following expression is -1% or smaller:

$$\Delta a/a = (a_d - a_e)/a_e$$

where  $a_d$  is a lattice constant of the current diffusion layer, and  $a_e$  is a lattice constant of the light-emitting structure.